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September 2014



FOD8383 2.5 A Output Current, High-Speed, MOSFET/IGBT Gate Drive Optocoupler in Optoplanar[®] Wide-Body SOP 5-Pin

Features

- Reliable and High-Voltage Insulation with Greater than 10 mm Creepage and Clearance Distance and 0.5 mm Internal Insulation Distance
- 2.5 A Output Current Driving Capability for Medium-Power IGBT/MOSFET
 - P-Channel MOSFET at Output Stage Enables Output Voltage Swing Close to Supply Rail
- 35 kV/µs Minimum Common Mode Rejection
- Wide Supply Voltage Range: 15 V to 30 V
- Fast Switching Speed Over Full Operating Temperature Range
 - 210 ns Maximum Propagation Delay
 - 65 ns Maximum Pulse-Width Distortion
- Under-Voltage Lockout (UVLO) with Hysteresis
- Extended Industrial Temperate Range: -40°C to 100°C
- Safety and Regulatory Approvals:
 - UL1577, 5,000 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 1,414 V Peak Working Insulation Voltage

Applications

- AC and Brushless DC Motor Drives
- Industrial Inverter
- Uninterruptible Power Supply
- Induction Heating
- Isolated IGBT/Power MOSFET Gate Drive

Related Resources

- FOD3184—3 A Output Current, High-Speed MOSFET/IGBT Gate Drive Optocoupler Datasheet
- www.fairchildsemi.com/products/opto/

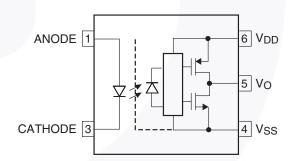
Description

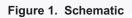
The FOD8383 is a 2.5 A output current gate drive optocoupler capable of driving medium-power IGBT/ MOSFETs. It is ideally suited for fast-switching driving of power IGBT and MOSFET used in motor-control inverter applications and high-performance power systems.

The FOD8383 utilizes Fairchild's Optoplanar[®] coplanar packaging technology and optimized IC design to achieve reliable high-insulation voltage and high-noise immunity.

It consists of an Aluminum Gallium Arsenide (AlGaAs) Light-Emitting Diode (LED) optically coupled to an integrated circuit with a high-speed driver for push-pull MOSFET output stage. The device is housed in a wide body, 5-pin, small-outline, plastic package.

Functional Schematic





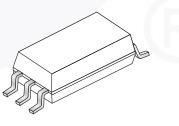
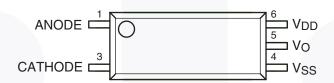


Figure 2. Package Outline

Truth Table

LED	V _{DD} – V _{SS} "Positive Going" (Turn-on)	V _{DD} _V _{SS} "Positive Going" (Turn-off)	vo
Off	0 V to 30 V	0 V to 30 V	LOW
On	0 V to 11.5 V	0 V to 10 V	LOW
On	11.5 V to 14.5 V	10 V to 13 V	Transition
On	14.5 V to 30 V	13 V to 30 V	HIGH

Pin Configuration





Pin Definitions

Pin #	Name	Description
1	Anode	LED Anode
3	Cathode	LED Cathode
4	V _{SS}	Negative Supply Voltage
5	Vo	Output Voltage
6	V _{DD}	Positive Supply Voltage

Safety and Insulation Ratings

As per DIN EN/IEC60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Тур.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Mains Voltage < 150 V _{RMS}		I–IV		
	For Rated Mains Voltage < 300 V _{RMS}		I–IV		
	For Rated Mains Voltage < 450 V _{RMS}		I–IIII		
	For Rated Mains Voltage < 600 V _{RMS}		I–III		
	Climatic Classification		40/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
N/	Input-to-Output Test Voltage, Method b, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC	2651			V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method a, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC	2262			V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	1414			V _{peak}
V _{IOTM}	Highest Allowable Over Voltage	8000			V _{peak}
	External Creepage	10.0			mm
	External Clearance	10.0			mm
	Insulation Thickness	0.5			mm
	Safety Limit Values – Maximum Values Allowed in the Event of a Failure				
Τ _S	Case Temperature	150			°C
I _{S,INPUT}	Input Current	200			mA
P _{S,OUTPUT}	Output Power	600			mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V	10 ⁹			Ω

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Value	Units	
T _{STG}	Storage Temperature	-40 to +125	°C	
T _{OPR}	Operating Temperature	-40 to +100	°C	
TJ	Junction Temperature	-40 to +125	°C	
–	Lead Solder Temperature	260 for 10 s	°C	
T _{SOL}	Refer to Reflow Temperature Profile on page 15.	200 101 10 5		
I _{F(AVG)}	Average Input Current	25	mA	
V _R	Reverse Input Voltage	5.0	V	
I _{O(PEAK)}	Peak Output Current ⁽¹⁾	3.0	A	
$V_{DD} - V_{SS}$	Supply Voltage	-0.5 to 35	V	
V _{O(PEAK)}	Peak Output Voltage	0 to V _{DD}	V	
PDI	Input Power Dissipation ⁽²⁾⁽⁴⁾	45	mW	
PD _O	Output Power Dissipation ⁽³⁾⁽⁴⁾	500	mW	

Notes:

1. Maximum pulse width = 10 μ s, maximum duty cycle = 0.2%.

- 2. No derating required across operating temperature range.
- 3. Derate linearly from 25°C at a rate of 5.2 mW/°C.
- 4. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
T _A	Ambient Operating Temperature	-40	100	°C
$V_{DD} - V_{SS}$	Supply Voltage	15	30	V
I _{F(ON)}	Input Current (ON)	10	16	mA
V _{F(OFF)}	Input Voltage (OFF)	0	0.8	V

Isolation Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	$\begin{split} T_{A} &= 25^{\circ}\text{C}, \text{ R.H.} < 50\%, \text{ t} = 60 \text{ s}, \\ I_{I-O} &\leq 20 \mu\text{A}, \text{ 50 } \text{Hz}^{(5)(6)} \end{split}$	5,000			V _{RMS}
R _{ISO}	Isolation Resistance	$V_{I-O} = 500 V^{(5)}$		10 ¹¹		Ω
C _{ISO}	Isolation Capacitance	V_{I-O} = 0 V, Frequency = 1.0 MHz ⁽⁶⁾		1		pF

Apply over all recommended conditions; typical value is measured at $T_A = 25^{\circ}C$.

Notes:

5. Device is considered a two-terminal device: pins 1 and 3 are shorted together and pins 4, 5 and 6 are shorted together.

6. 5,000 VAC_{RMS} for 1 minute duration is equivalent to 6,000 VAC_{RMS} for 1 second duration.

Electrical Characteristics

Apply over all recommended conditions, typical value is measured at V_{DD} = 30 V, V_{SS} = Ground, T_A = 25°C unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	Figure
V _F	Input Forward Voltage		1.10	1.43	1.80	V	19
$\Delta(V_{F} / T_{A})$	Temperature Coefficient of Forward Voltage	I _F = 10 mA		-1.5		mV/°C	
BV _R	Input Reverse Breakdown Voltage	I _R = 10 μA	5			V	
C _{IN}	Input Capacitance	f = 1 MHz, V _F = 0 V		60		pF	
1	High Level Output	V _{OH} = V _{DD} – 1 V		-0.9	-0.5	А	4, 6
I _{OH}	Current ⁽¹⁾	V _{OH} = V _{DD} - 6 V			-2.5	А	4, 6, 22
1	Low Level Output	V _{OL} = V _{SS} + 1 V	0.5	1.0		А	7, 9
I _{OL}	Current ⁽¹⁾	V _{OL} = V _{SS} + 6 V	2.5			А	7, 9, 21
M	High Level Output	I _F = 10 mA, I _O = -2.5 A	V _{DD} – 7.0			V	4
V _{OH}	Voltage ⁽⁷⁾⁽⁸⁾	I _F = 10 mA, I _O = -100 mA	V _{DD} – 0.5			V	4, 5, 23
V	Low Level Output	I _F = 0 mA, I _O = 2.5 A			V _{SS} + 7.0	V	7
V _{OL}	Voltage ⁽⁷⁾⁽⁸⁾	I _F = 0 mA, I _O = 100 mA			V _{SS} + 0.5	V	8, 24
I _{DDH}	High Level Supply Current	V _O = Open, I _F = 7 to 16 mA		2.9	3.5	mA	10, 11, 25
I _{DDL}	Low Level Supply Current	V _{O =} Open, V _F = 0 to 0.8 V		2.8	3.5	mA	10, 11, 26
I _{FLH}	Threshold Input Current Low-to-High	I _O = 0 mA, V _O > 5 V		3.1	7.5	mA	12, 18, 27
V _{FHL}	Threshold Input Voltage High-to-Low	I _O = 0 mA, V _O < 5 V	0.8			V	28
V _{UVLO+}	Under-Voltage Lockout	I _F = 10 mA, V _O > 5 V	11.5	13.0	14.5	V	20, 29
V _{UVLO-}	Threshold	I _F = 10 mA, V _O < 5 V	10.0	11.5	13.0	V	20, 29
UVLO _{HYS}	Under-Voltage Lockout Threshold Hysteresis			1.5		V	

Notes:

In this test, V_{OH} is measured with a dc load current of 100 mA. When driving capacitive load V_{OH} will approach V_{DD} as I_{OH} approaches 0 A.

8. Maximum pulse width = 1 ms, maximum duty cycle = 20%.

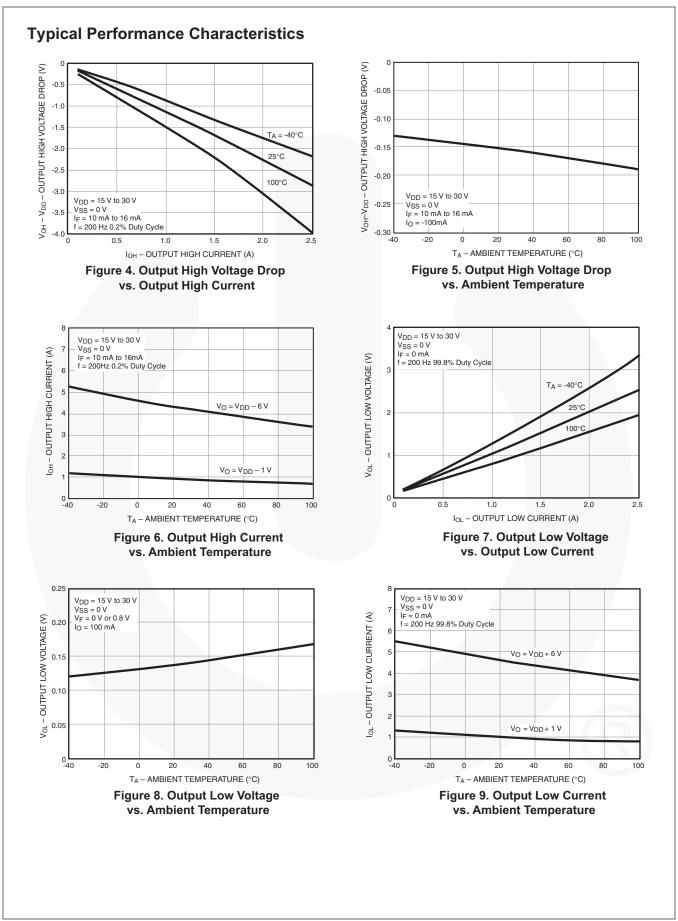
Switching Characteristics

Apply over all recommended conditions, typical value is measured at V_{DD} = 30 V, V_{SS} = Ground, T_A = 25°C unless otherwise specified.

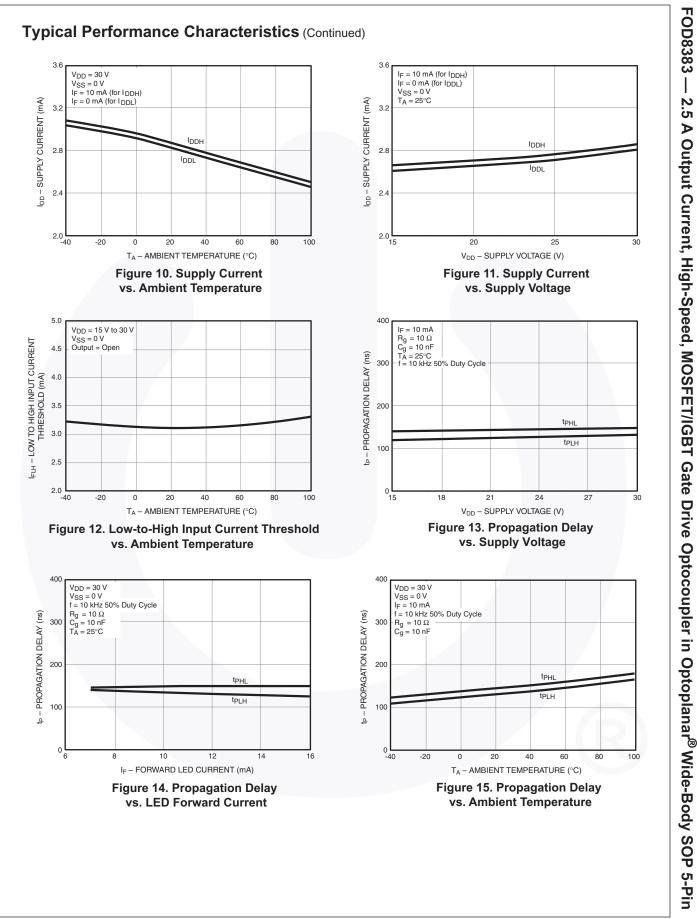
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	Figure
t _{PHL}	Propagation Delay Time to Logic LOW Output ⁽⁹⁾		50	145	210	ns	13, 14, 15, 16, 17, 30
t _{PLH}	Propagation Delay Time to Logic HIGH Output ⁽¹⁰⁾	1 - 7 = 7 = 16 = 16	50	135	210	ns	13, 14, 15, 16, 17, 30
PWD	Pulse Width Distortion ⁽¹¹⁾ t _{PHL} – t _{PLH}	$I_F = 7$ mA to 16 mA, $R_g = 10 \Omega$, $C_g = 10$ nF, f = 250 kHz, Duty Cycle = 50%		25	65	ns	
PDD (Skew)	Propagation Delay Difference Between Any Two Parts ⁽¹²⁾		-90		90		
t _R	Output Rise Time (10% to 90%)			35		ns	30
t _F	Output Fall Time (90% to 10%)			25		ns	30
t _{ULVO ON}	ULVO Turn-On Delay	I _F = 10 mA, V _O > 5 V		1.7		μs	
t _{ULVO OFF}	ULVO Turn-Off Delay	I _F = 10 mA, V _O < 5 V		0.1		μs	
CM _H	Common Mode Transient Immunity at Output HIGH		35	50		kV/µs	31
CM _L	Common Mode Transient Immunity at Output LOW	$T_A = 25^{\circ}C, V_{DD} = 30 V,$ $V_F = 0 V, V_{CM} = 1500 V^{(14)}$	35	50		kV/µs	31

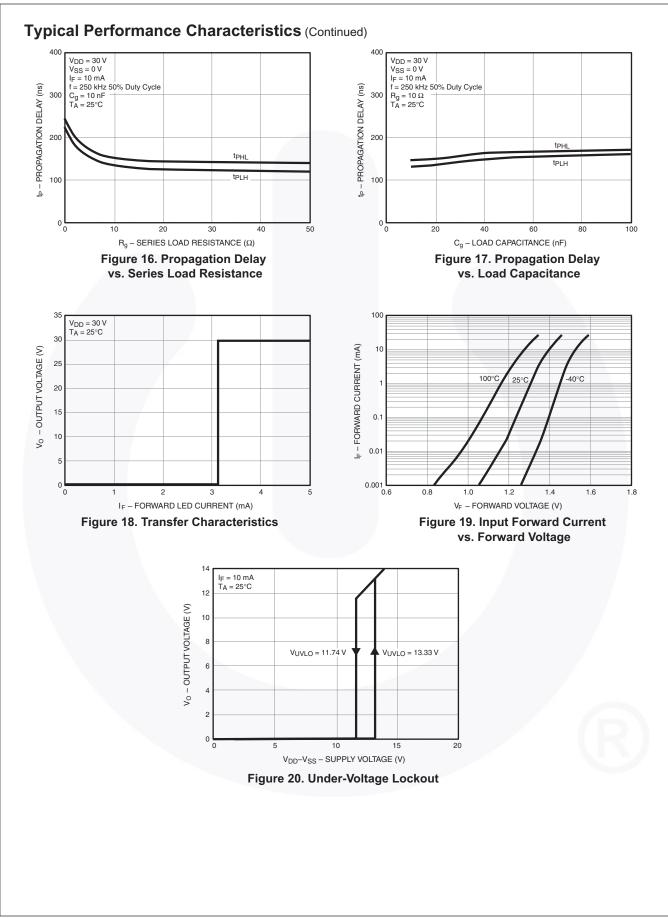
Notes:

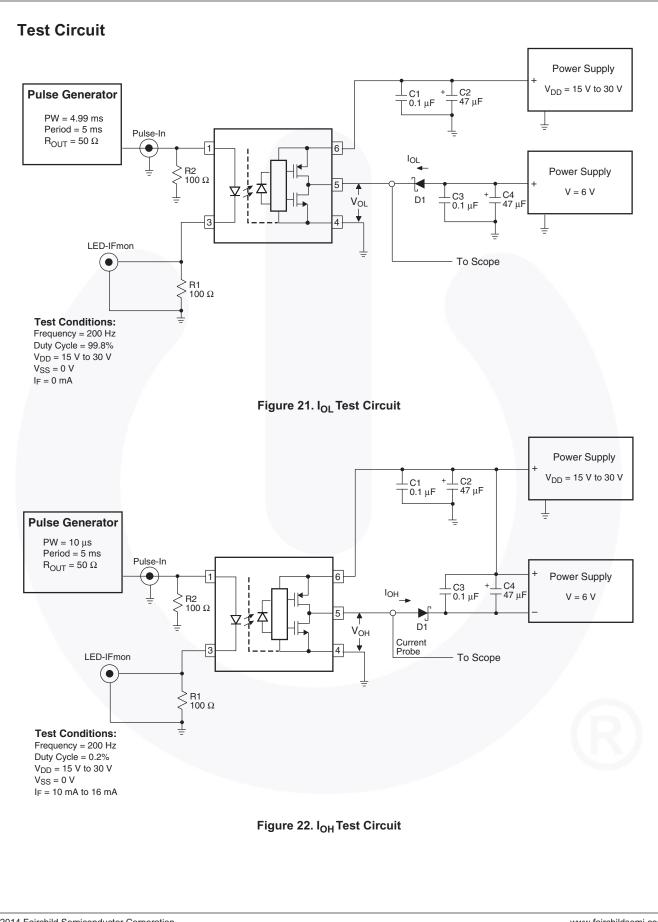
- Propagation delay t_{PHL} is measured from the 50% level on the falling edge of the input pulse to the 50% level of the falling edge of the V_O signal.
- 10. Propagation delay t_{PLH} is measured from the 50% level on the rising edge of the input pulse to the 50% level of the rising edge of the V_O signal.
- 11. PWD is defined as $|t_{PHL} t_{PLH}|$ for any given device.
- 12. The difference between t_{PHL} and t_{PLH} between any two FOD8383 parts under the same operating conditions, with equal loads.
- 13. Common mode transient immunity at output high is the maximum tolerable negative dVcm/dt on the trailing edge of the common mode impulse signal, V_{CM} , to ensure that the output remains high (i.e., $V_O > 15.0$ V).
- 14. Common mode transient immunity at output low is the maximum tolerable positive dVcm/dt on the leading edge of the common pulse signal, V_{CM} , to ensure that the output remains low (i.e., $V_O < 1.0$ V).

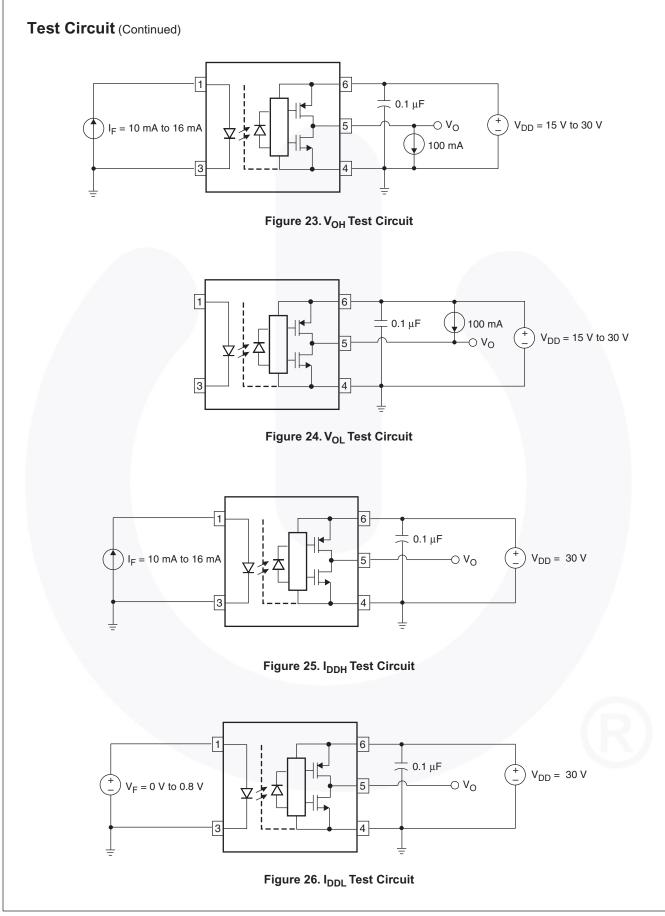


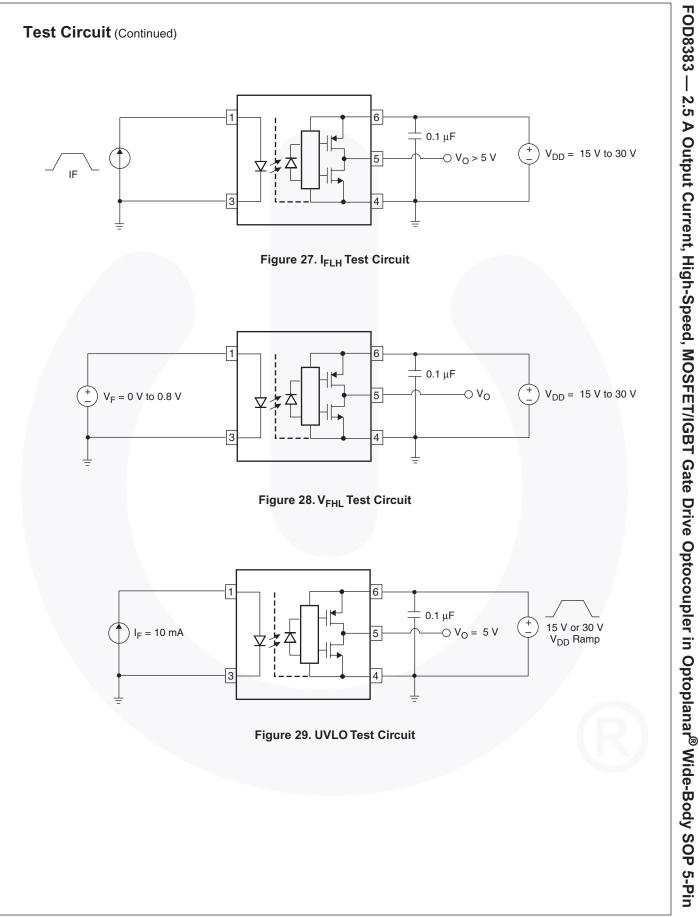
FOD8383 — 2.5 A Output Current, High-Speed, MOSFET/IGBT Gate Drive Optocoupler in Optoplanar[®] Wide-Body SOP 5-Pin

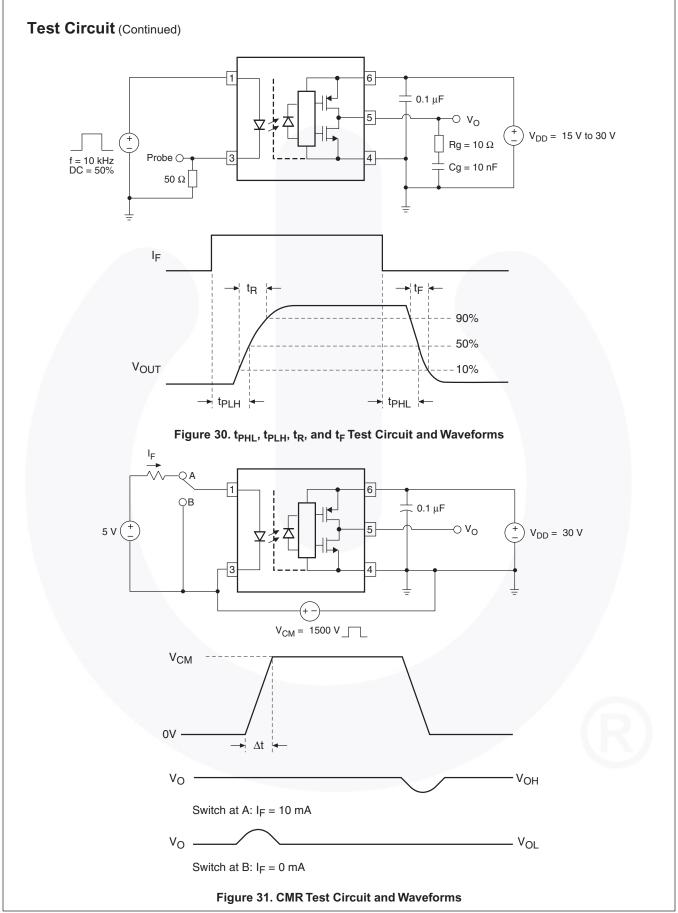


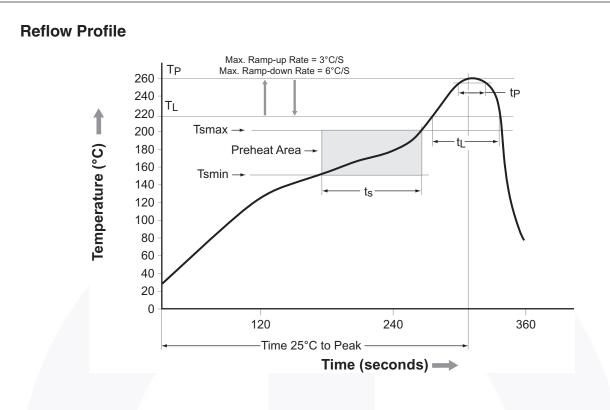












Pb-Free Assembly Profile
150°C
200°C
60 s to 120 s
3°C/second maximum
217°C
60 s to 150 s
260°C +0°C / –5°C
30 s
6°C/s maximum
8 minutes maximum

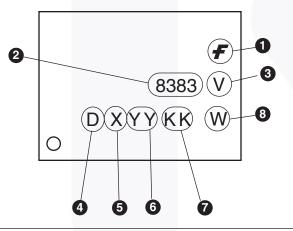
Figure 32. Reflow Profile

Ordering Information

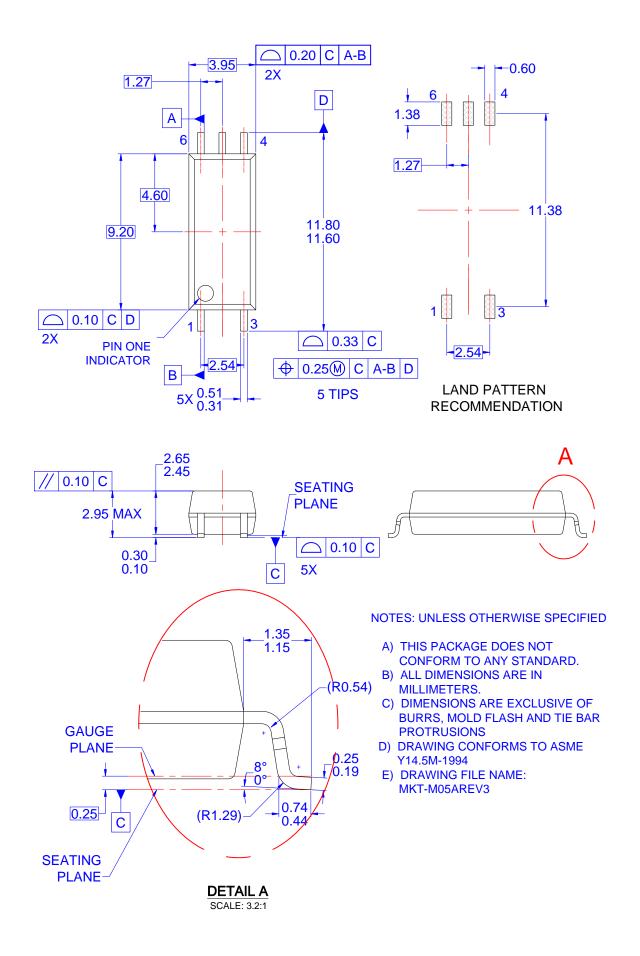
Part Number	Package	Packing Method
FOD8383	Wide Body SOP 5-Pin	Tube (100 units per tube)
FOD8383R2	Wide Body SOP 5-Pin	Tape and Reel (1,000 units per reel)
FOD8383V	Wide Body SOP 5-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 units per tube)
FOD8383R2V	Wide Body SOP 5-Pin, DIN EN/ IEC60747-5-5 Option	Tape and Reel (1,000 units per reel)

All packages are lead free per JEDEC: J-STD-020B standard.

Marking Information



Definitions				
1	Fairchild logo			
2	Device number, e.g., '8383' for FOD8383			
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)			
4	Plant code, e.g., 'D'			
5	Last digit year code, e.g., 'C' for 2012			
6	Two-digit work week ranging from '01' to '53'			
7	Lot traceability code			
8	Package assembly code, W			



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